



1mm extended InGaAs PIN PD

(P/N.: ex-InGaAs-1000-01)

Features

- 1.0mm active area diameter
- Low dark current and high responsivity

Absolute Maximum Ratings

Parameter	Symbol	Min	Typ	Max	Unit
Operating Case Temperature	T _C	-40	-	85	°C
Storage Temperature	T _{STG}	-40	-	125	°C
Lead Soldering Temperature	T _{SOL}	-	-	260 (5s)	°C
Reverse voltage	V _R	-		0.5	V
Reverse current	I _R	-	-	1.0	mA

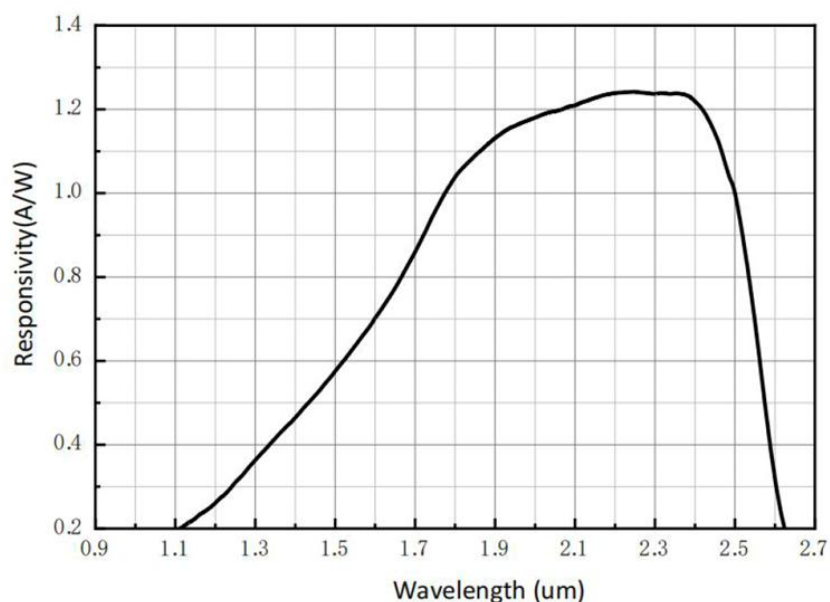
Opto-Electrical Characteristics

V_R = -0.5V, 25 °C

Parameter	Symbol	Min	Typ	Max	Unit
Active area diameter	Φ	-	1000	-	μm
Wavelength range	λ	1200	-	2600	nm
1.55 μm Responsivity	R	0.6	0.95	-	A/W
2.0 μm Responsivity		-	1.2	-	A/W
Capacitance @ f = 1MHz	C _t	-	600	-	pF
Dark current	I _D	-	10	30	uA

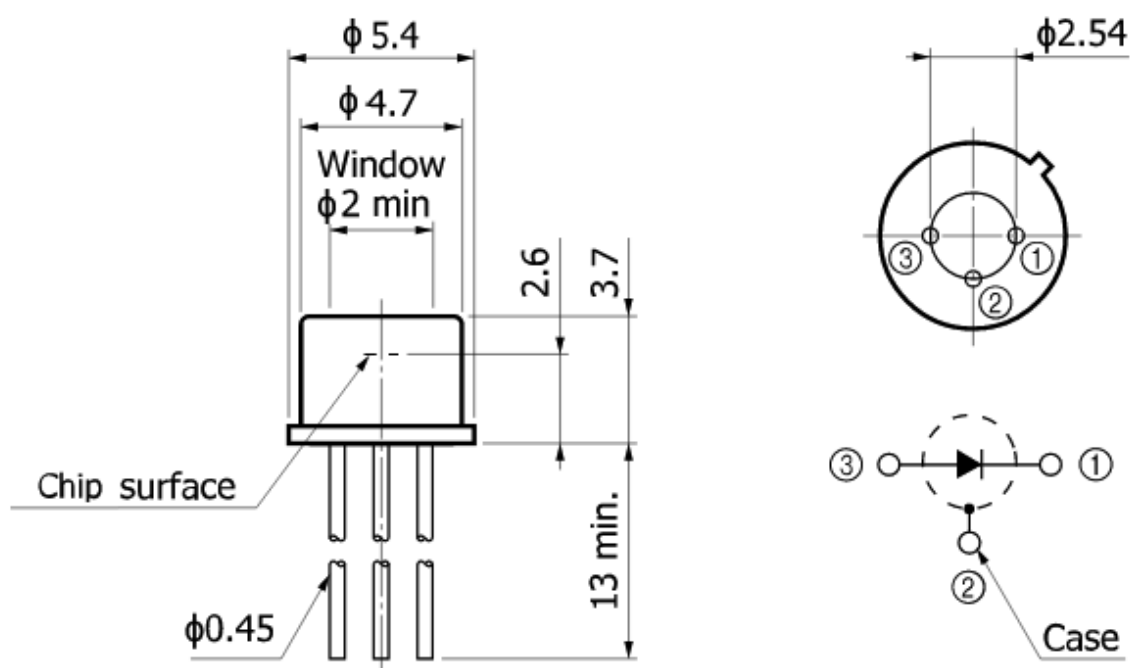
Typical Performance at 25°C

die responsivity only



Dimensional outlines (unit = mm)

TO

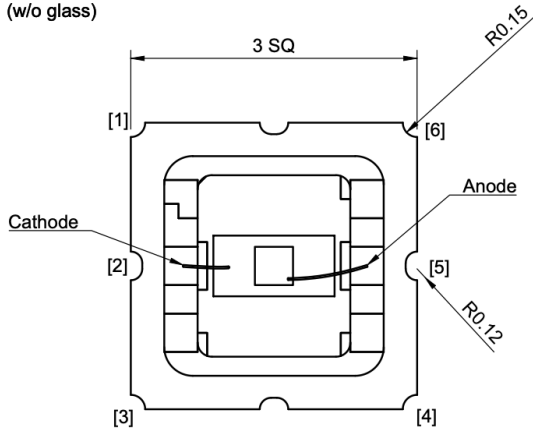


Package can be customized

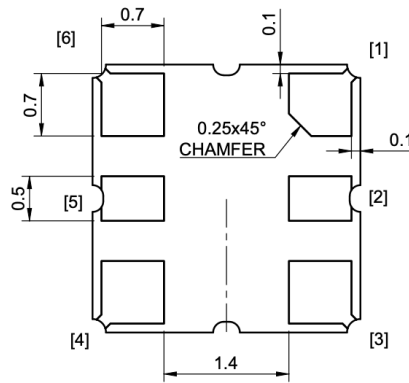


SMD

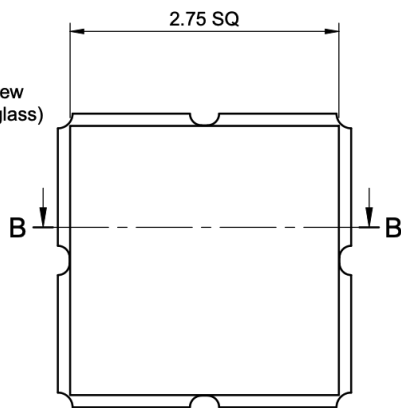
Top view
(w/o glass)



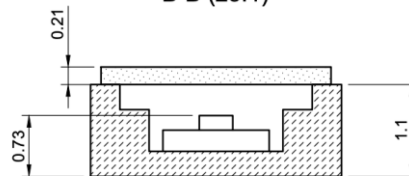
Bottom view



Top view
(with glass)



B-B (25:1)



Package can be customized